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Silicon PNP Power Transistor**2SA1640****DESCRIPTION**

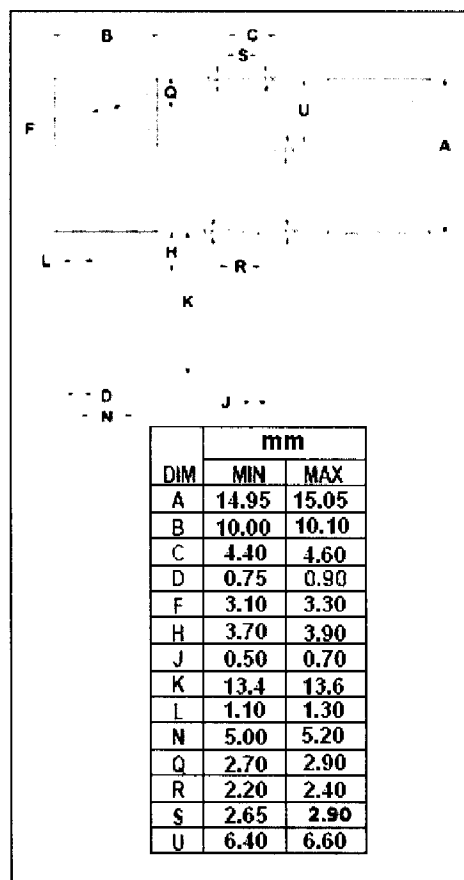
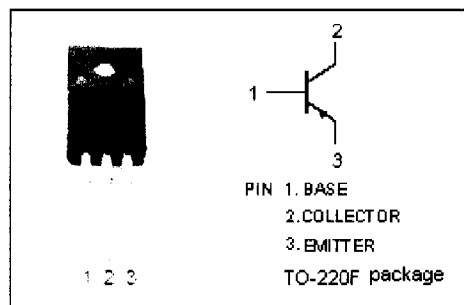
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -30V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -0.4V(\text{Max})@ (I_C = -3A, I_B = -0.1A)$

APPLICATIONS

- Designed for switching regulator, driver and power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Silicon PNP Power Transistor**2SA1640****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-30			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-5			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-30			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -0.1A			-0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -3A; I _B = -0.1A			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -30V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.2A; V _{CE} = -2V	100			
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -10V	20			MHz